## N-Channel 100-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

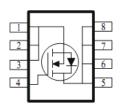
<b>Typical</b>	An	plica	ation	is:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$ $I_D(A)$			
100	26 @ V <sub>GS</sub> = 10V	9		
	$36 @ V_{GS} = 4.5V$	7.6		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage		$V_{DS}$	100	V		
Gate-Source Voltage	$V_{GS}$	±20	٧			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C		9			
Continuous Drain Current	T <sub>A</sub> =70°C	l <sub>D</sub>	7.5	Α		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	50				
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	4.5	Α			
Dower Dissipation a	T <sub>A</sub> =25°C		3.1	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	] 'D	2.2	V V		
Operating Junction and Storage Temperature Range			-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter			Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Ambient	Steady State	ГХ⊕ЈА	80	C/VV	

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

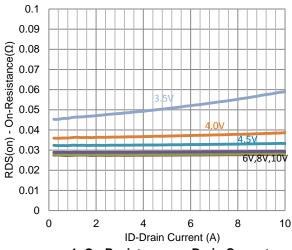
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $ID = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	1 10 uA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A}$			26	mΩ	
Dialii-Source Ori-Nesistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 5.6 \text{ A}$			36	11122	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 6.0 \text{ A}$		20		S	
Diode Forward Voltage	$V_{SD}$	$I_{S} = 2 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic							
Total Gate Charge	$Q_g$			15.4			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, ID = 6.0 \text{ A}$		3.9		nC	
Gate-Drain Charge	$Q_{gd}$			9.1			
Turn-On Delay Time	t <sub>d(on)</sub>			7.5			
Rise Time	t <sub>r</sub>	$V_{DD}$ = 50 V, $R_L$ = 8.3 $\Omega$ , $I_D$ = 6.0 A,		15		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN}$ = 10 V, $R_{GEN}$ = 6 $\Omega$		53		ns	
Fall Time	t <sub>f</sub>			25			
Input Capacitance	C <sub>iss</sub>			1216			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		154		pF	
Reverse Transfer Capacitance	$C_{rss}$			131			

#### Notes

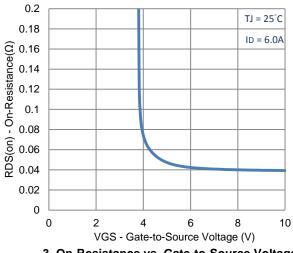
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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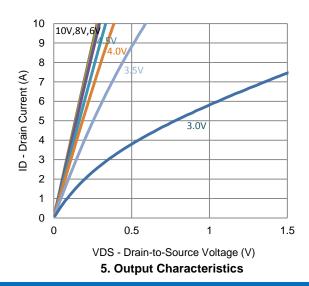
## **Typical Electrical Characteristics**

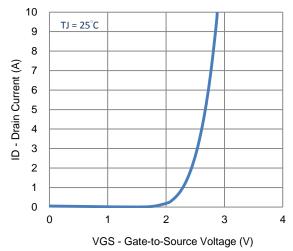


#### 1. On-Resistance vs. Drain Current

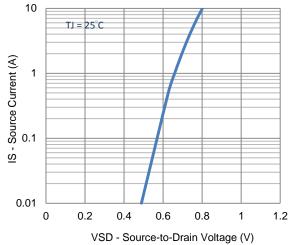


3. On-Resistance vs. Gate-to-Source Voltage

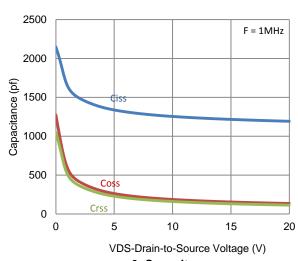




2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



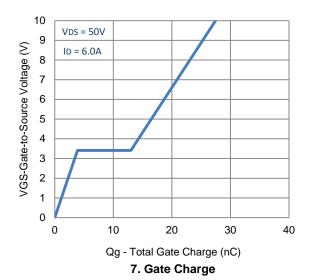
## **Typical Electrical Characteristics**

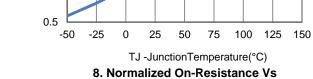
2.5

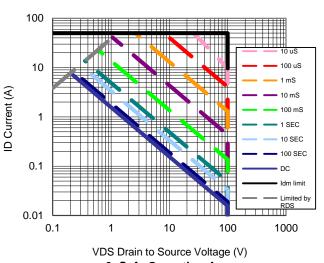
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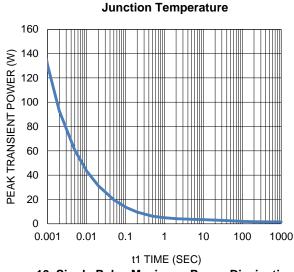
1.5

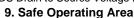
 $RDS(on) - On-Resistance(\Omega) \\ (Normalized)$ 

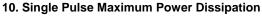


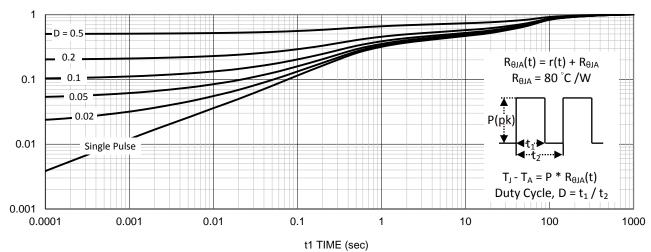








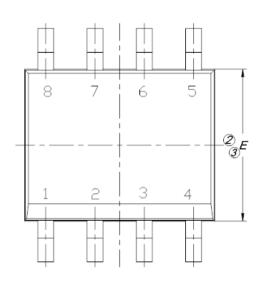


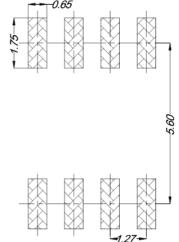


11. Normalized Thermal Transient Junction to Ambient

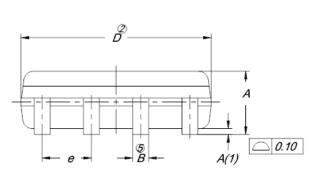
### **Package Information**

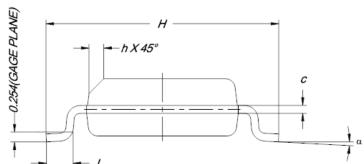
Land Pattern (Only for Reference)





DIM.	MILLIMETERS					
	MIN.	NOM.	MAX.			
Α	1.35	1.55	1.75			
A(1)	0.10	0.18	0.25			
В	0.38	0.45	0.51			
С	0.19	0.22	0.25			
D	4.80	4.90	5.00			
E	3.80	3.90	4.00			
е	1.27 BSC					
Н	5.80	6.00	6.20			
L	0.50	0.72	0.93			
α	0°	4°	8°			
h	0.25	0.38	0.50			





#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- 5. Dimension "B" Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess Of "B" Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The Foot.

## **Ordering Information**

# AM4492N-T1-XX

A: Analog Power

- M: MOSFET

- 4492: Part number

– N: N-Channel

– T1: Tape & reel

XX: Blank: Standard

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PF: Leadfree